



140V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Features

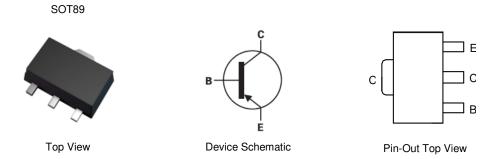
- BV_{CEO} > -140V
- I_C = -3A Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Very Low Saturation Voltage
- $R_{SAT} = 85m\Omega @ I_C 3A$ for Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXTP2014ZQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.05 grams (Approximate)

Applications

- Motor Driving
- Line Switching
- **High Side Switches**
- Subscriber Line Interface Cards (SLIC)



Ordering Information (Note 4)

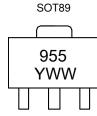
Pa	art Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXT	P2014ZQTA	Automotive	955	7	12	1000
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/guality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free. "Green" and

Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



955 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 9 = 2019) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-180	V
Collector-Emitter Voltage	V _{CEO}	-140	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	lc	-3	A
Peak Pulse Current	I _{CM}	-10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	L L	1.5 12	W mW/°C	
Linear Derating Factor	(Note 6)	PD	2.1 16.8		
Thermal Desistance Junction to Ambient	(Note 5)	R _{eja}	83	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{ƏJA}	60	-C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

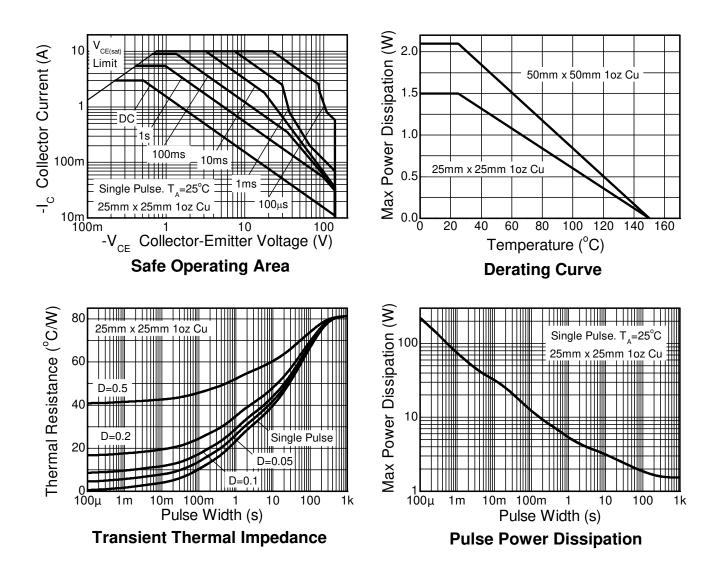
ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge — Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge — Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 25mm × 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air for a device included with the collecton lead on 25mm x 25mm 102 copper that conditions whilst operating in steady-state.
 Same as Note 5, except the device is mounted on 50mm × 50mm 102 copper.
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





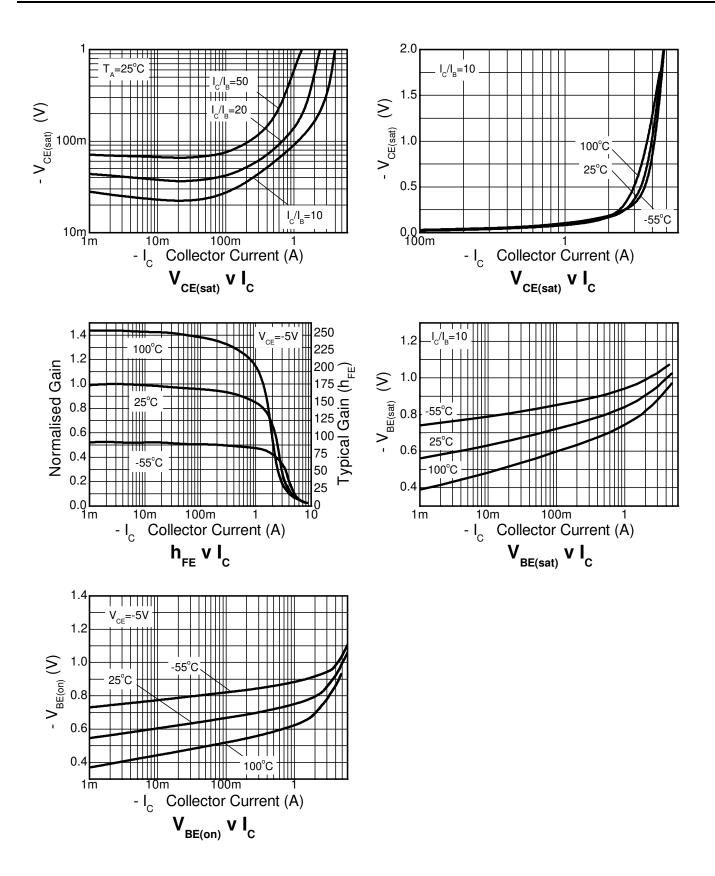
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		-180	-200	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage		-180	-200	—	V	$I_{C} = -1\mu A, R_{B} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-140	-160	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7.0	-8.0	—	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}		< -1 —	-20 -0.5	nA μA	V _{CB} = -150V V _{CB} = -150V, T _A = +100°C
Collector Cutoff Current	l _{CER} R ≤ 1kΩ		< -1 —	-20 -0.5	nA μA	V _{CB} = -150V V _{CB} = -150V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	_	< -1	-10	nA	V _{EB} = -6V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	_	-37 -50 -80 -255	-60 -75 -115 -330	mV	I _C = -0.1A, I _B = -5mA I _C = -0.5A, I _B = -50mA I _C = -1A, I _B = -100mA I _C = -3A, I _B = -300mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	_	-910	-1010	mV	I _C = -3A, I _B = -300mA
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(on)}	_	-800	-900	mV	$I_{C} = -3A, V_{CE} = -5V$
DC Current Gain (Note 8)	h _{FE}	100 100 45 —	225 200 100 5	 300 	_	$\begin{split} I_{C} &= -10 \text{mA}, \ V_{CE} &= -5 \text{V} \\ I_{C} &= -1 \text{A}, \ V_{CE} &= -5 \text{V} \\ I_{C} &= -3 \text{A}, \ V_{CE} &= -5 \text{V} \\ I_{C} &= -10 \text{A}, \ V_{CE} &= -5 \text{V} \end{split}$
Transition Frequency	fT	_	120	_	MHz	V _{CE} = -10V, I _C = -100mA, f = 50MHz
Output Capacitance	C _{OBO}		33	—	pF	V _{CB} = -10V, f = 1MHz
Switching Time	t _{ON}	_	42	_	ns	$V_{CC} = -50V, I_C = -1A,$
-	t _{OFF}	_	636	—		$I_{B1} = -I_{B2} = -100 \text{mA}$

Note: 8. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

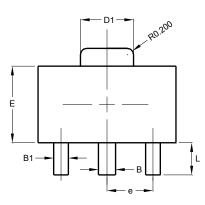


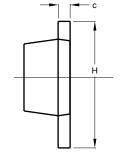


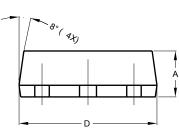
Package Outline Dimensions

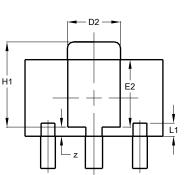
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







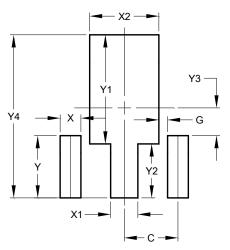


	SOT89						
Dim	Min	Max	Тур				
Α	1.40	1.60	1.50				
В	0.50	0.62	0.56				
B1	0.42	0.54	0.48				
С	0.35	0.43	0.38				
D	4.40	4.60	4.50				
D1	1.62	1.83	1.733				
D2	1.61	1.81	1.71				
Е	2.40	2.60	2.50				
E2	2.05	2.35	2.20				
е	-	-	1.50				
н	3.95	4.25	4.10				
H1	2.63	2.93	2.78				
L	0.90	1.20	1.05				
L1	0.327	0.527	0.427				
z	0.20	0.40	0.30				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		



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